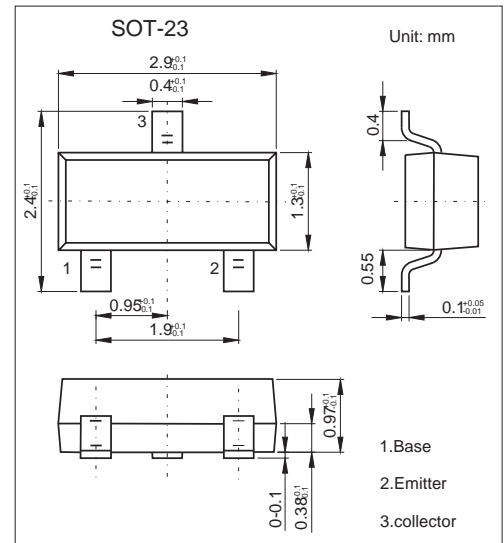


Features

"PNP Silicon
 "+LJ\$KROWDJH 7UDQVLVWRUV

0 (& + \$ 1 , & \$ / ' \$ 7 \$

"& DVVH\OH 62ROGHG SODVWLF
 "ORXQLQJ SRVLWLRQ DQ\



0 \$; , 0 8 0 5 \$ 7 , 1 * \$ 1 ' Å a ð 0

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	V _{CEO}	-200	V
Collector-base voltage	V _{CBO}	-200	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current-continuous	I _c	-500	mA
Total device dissipation FR-5 board *1			
@ TA = 25°C	P _D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal resistance, junction-to-ambient	R _{θJA}	556	°C/W
Total device dissipation alumina substrate *2			
@ TA = 25°C	P _D	300	mW
derate above 25°C		2.4	mW/°C
Thermal resistance, junction-to-ambient	R _{θJA}	417	°C/W
Junction and storage temperature	T _J , T _{stg}	-55 to +150	°C

* 1. FR-5 = 1.0 X 0.75 X 0.062 in.

* 2. Alumina = 0.4 X 0.3 X 0.024 in. 99.5% alumina.